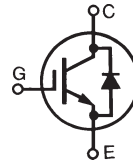


High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBH42N170 IXBT42N170



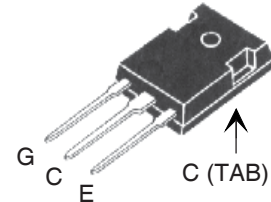
$$V_{CES} = 1700V$$

$$I_{C90} = 42A$$

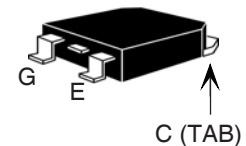
$$V_{CE(sat)} \leq 2.8V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ C$ to $150^\circ C$	1700	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	80	A
I_{LRMS}	Terminal Current Limit	75	A
I_{C90}	$T_C = 90^\circ C$	42	A
I_{CM}	$T_C = 25^\circ C$, 1ms	300	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 10\Omega$	$I_{CM} = 100$	A
(RBSOA)	Clamped inductive load	$V_{CES} \leq 1350$	V
P_C	$T_C = 25^\circ C$	360	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ C$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 (IXBH)



TO-268 (IXBT)



G = Gate C = Collector
E = Emitter TAB = Collector

Features

- High blocking voltage
- International standard packages
- Low conduction losses

Advantages

- Low gate drive requirement
- High power density

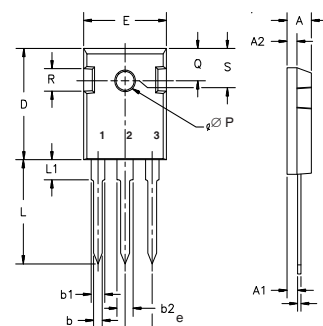
Applications:

- Switched-mode and resonant-mode power supplies
- Uninterruptible power supplies (UPS)
- Laser generator
- Capacitor discharge circuit
- AC switches

Symbol	Test Conditions ($T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 1.5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 42A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.7	2.8 V V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 42\text{A}$, $V_{CE} = 10\text{V}$, Note 1	24	32	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		3990	pF
C_{oes}			225	pF
C_{res}			70	pF
Q_g	$I_C = 42\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		188	nC
Q_{ge}			29	nC
Q_{gc}			76	nC
$t_{d(on)}$	Resistive Switching times, $T_J = 25^\circ\text{C}$ $I_C = 42\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 850\text{V}$, $R_G = 10\Omega$		37	ns
t_r			139	ns
$t_{d(off)}$			340	ns
t_f			665	ns
$t_{d(on)}$	Resistive Switching times, $T_J = 125^\circ\text{C}$ $I_C = 42\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 850\text{V}$, $R_G = 10\Omega$		36	ns
t_r			188	ns
$t_{d(off)}$			330	ns
t_f			740	ns
R_{thJC}				0.35 $^\circ\text{C/W}$
R_{thCS}	(TO-247)		0.25	$^\circ\text{C/W}$

TO-247 (IXBH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

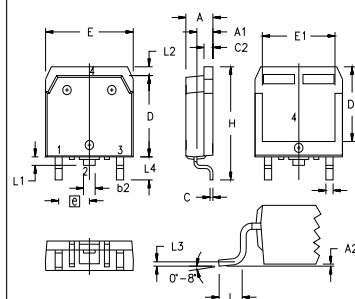
Dim.	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Reverse Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 42\text{A}$, $V_{GE} = 0\text{V}$			2.8 V
t_{rr}	$I_F = 21\text{A}$, $V_{GE} = 0\text{V}$, $-di_F/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		1.32	μs
I_{RM}			36	A

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-268 (IXBT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

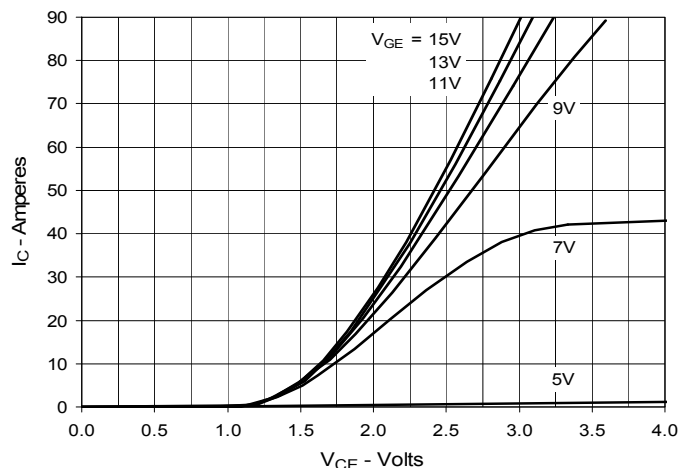


Fig. 2. Extended Output Characteristics
@ 25°C

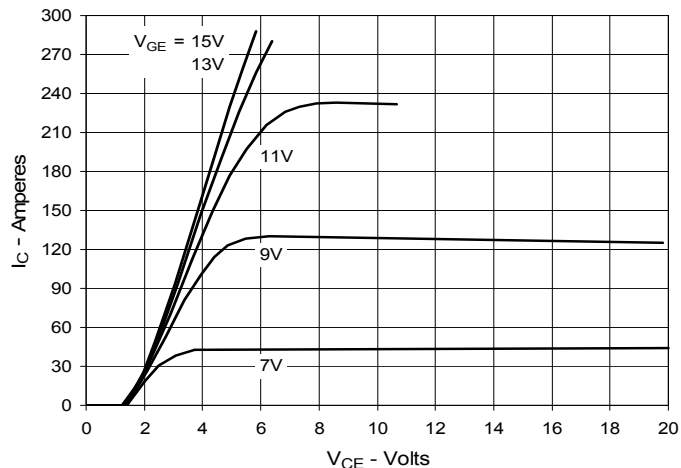


Fig. 3. Output Characteristics
@ 125°C

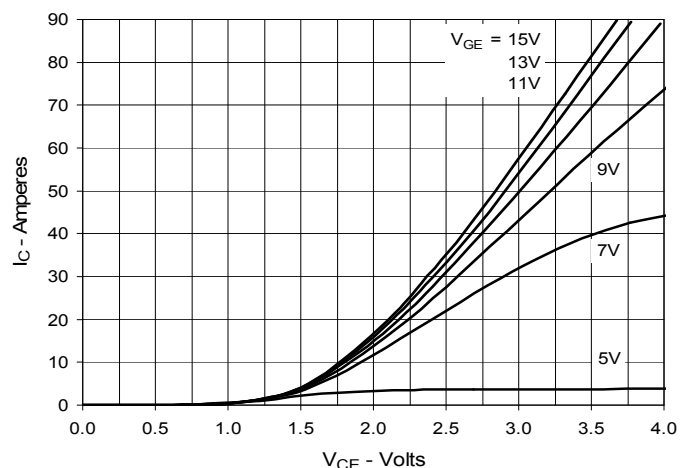


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

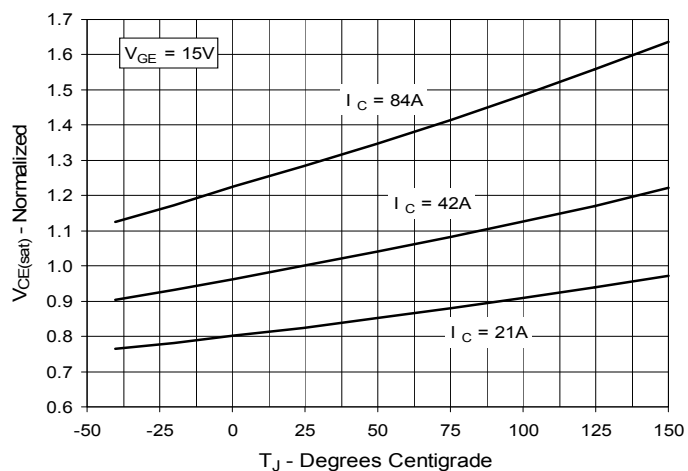


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

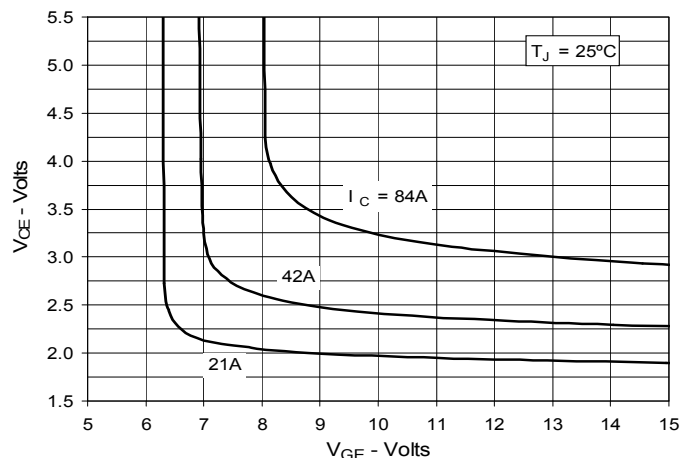


Fig. 6. Input Admittance

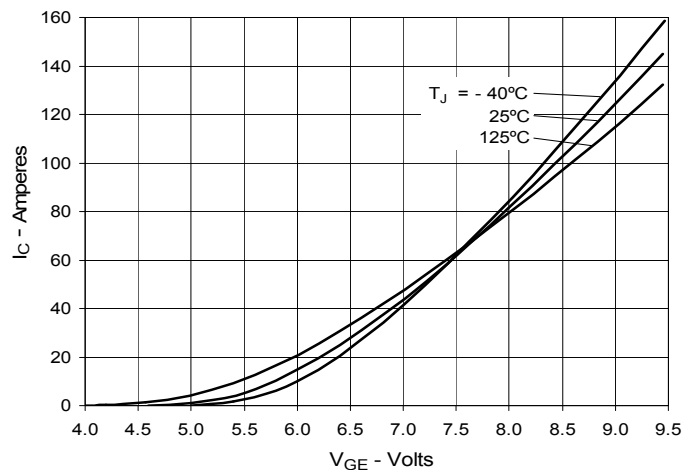


Fig. 7. Transconductance

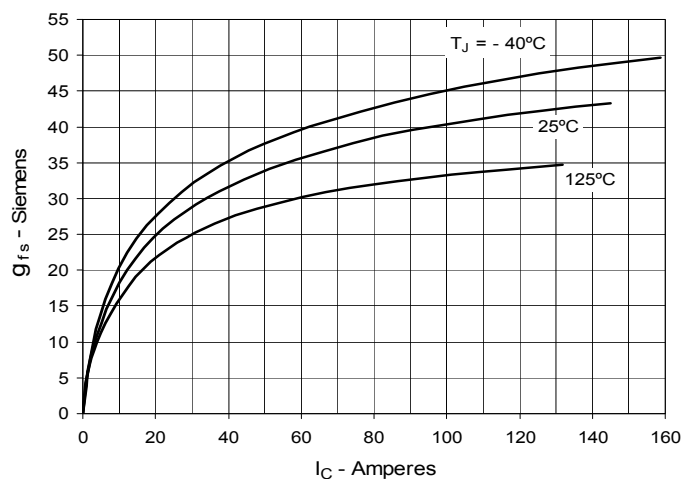


Fig. 8. Forward Voltage Drop of Intrinsic Diode

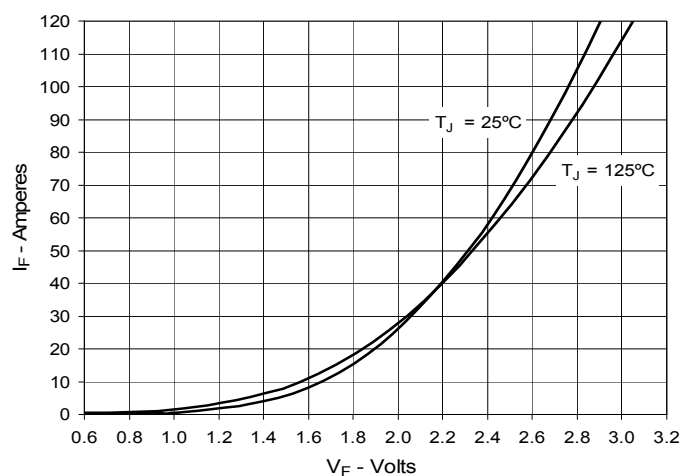


Fig. 9. Gate Charge

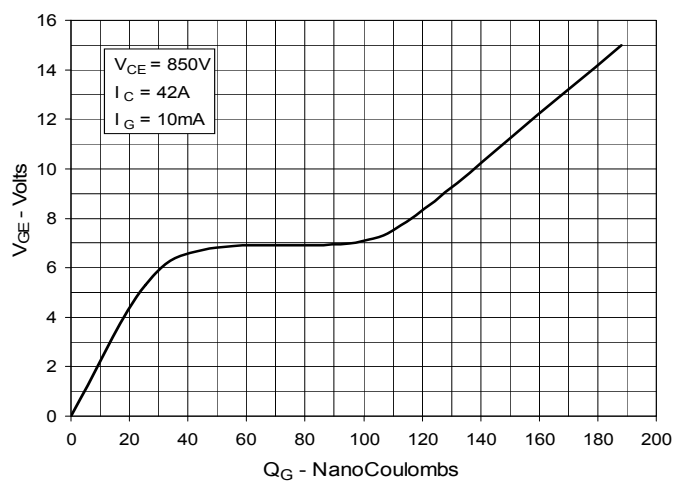


Fig. 10. Capacitance

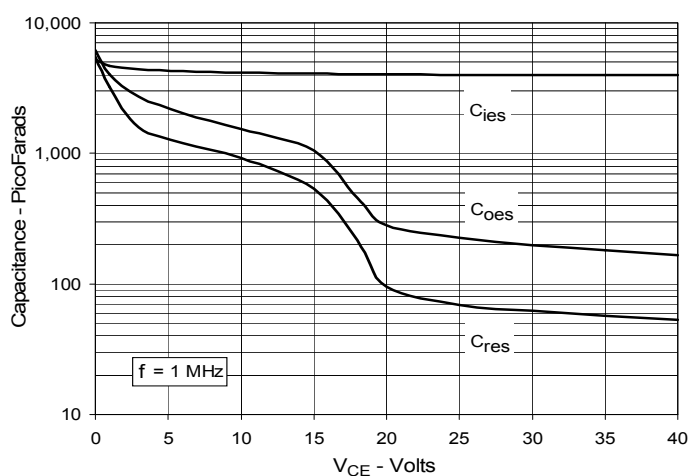


Fig. 11. Reverse-Bias Safe Operating Area

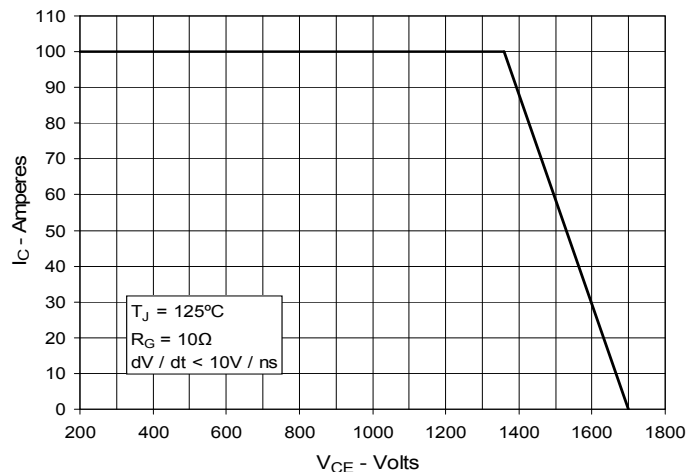


Fig. 12. Maximum Transient Thermal Impedance

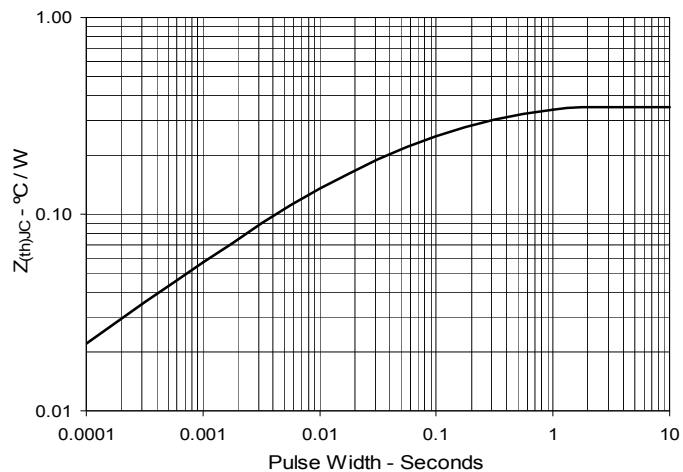


Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature

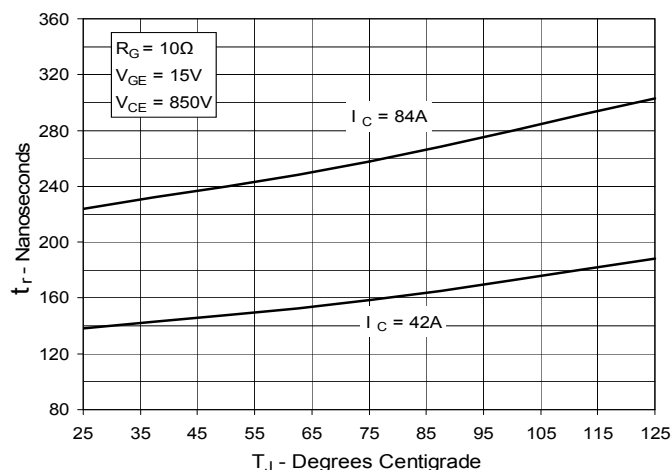


Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current

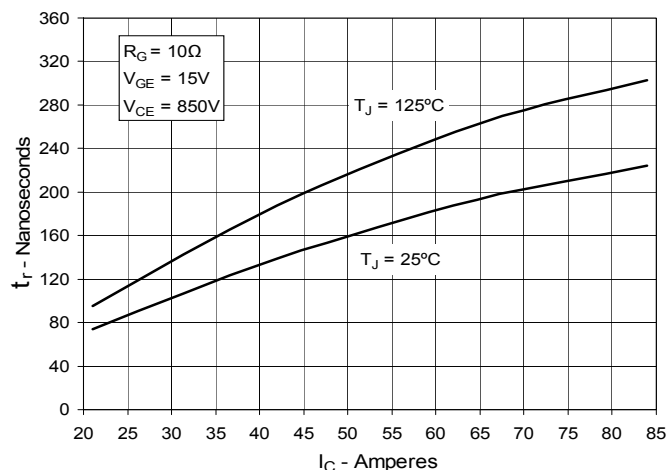


Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance

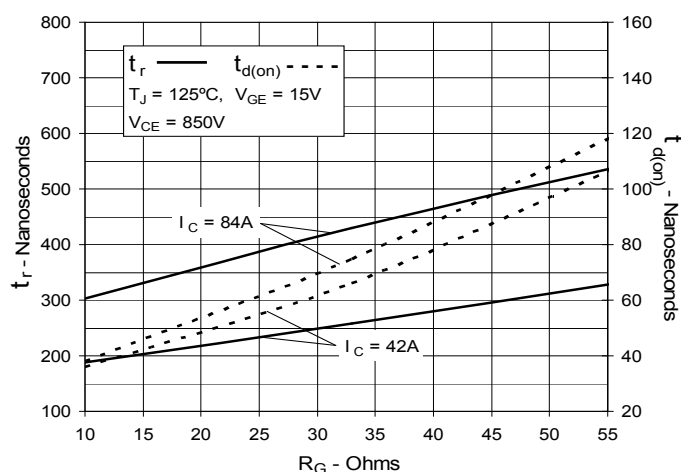


Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature

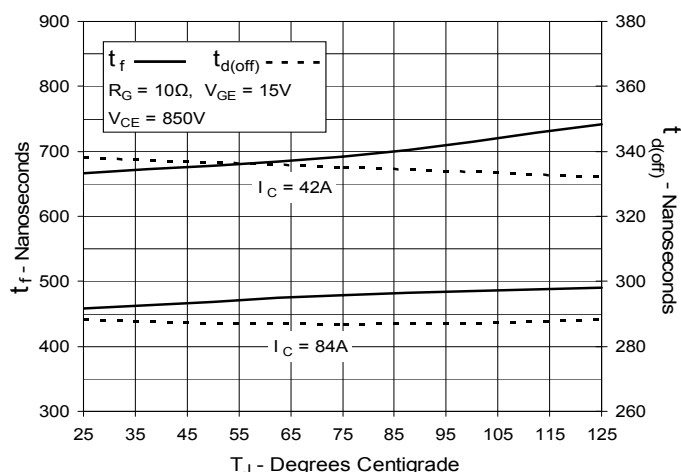


Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current

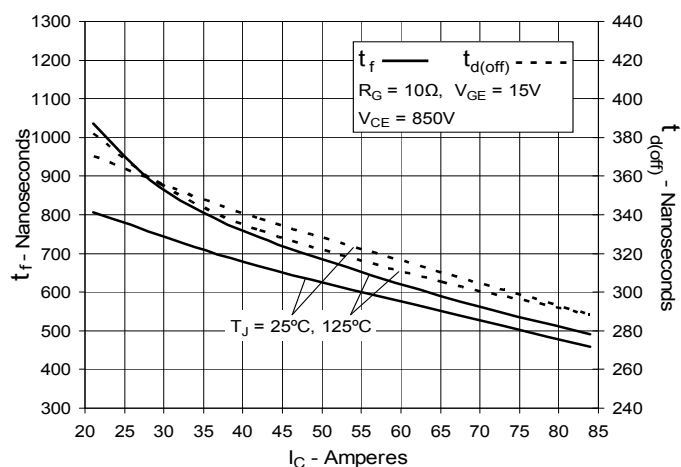


Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance

